



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

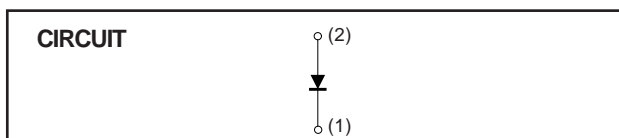
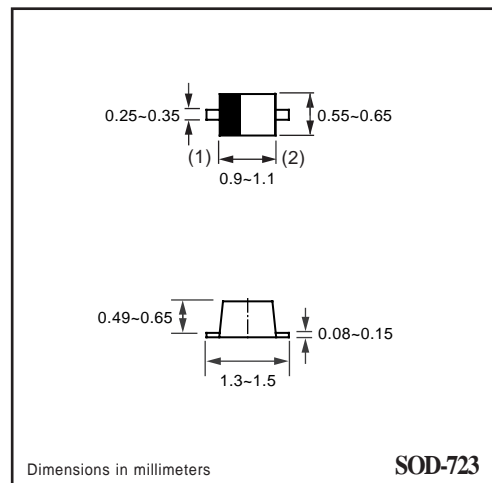
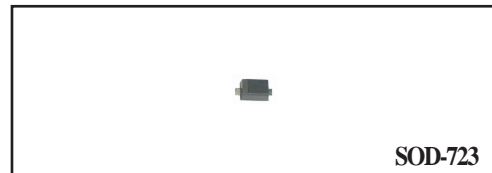
SURFACE MOUNT

SCHOTTKY BARRIER DIODE

VOLTAGE 45 Volts CURRENT 0.1 Ampere

CH501G-40GP

<p>APPLICATION</p> <p>* Low power rectification</p>
<p>FEATURE</p> <p>* Small surface mounting type. (SOD-723)</p> <p>* Low VF. (VF=0.43V Typ. at 100mA)</p> <p>* High reliability</p>
<p>CONSTRUCTION</p> <p>* Silicon epitaxial planar</p>
<p>MARKING</p> <p>* 1</p>



MAXIMUM RATINGS (At TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	CH501G-40GP	UNITS
Maximum Recurrent Peak Reverse Voltage	VRRM	45	Volts
Maximum RMS Voltage	VRMS	32	Volts
Maximum DC Blocking Voltage	VDC	40	Volts
Maximum Average Forward Rectified Current	Io	0.1	Amps
Peak Forward Surge Current at 8.3 mSec single half sine-wave	IFSM	1.0	Amps
Typical Junction Capacitance between Terminal (Note 1)	CJ	6.0	pF
Maximum Operating Temperature Range	TJ	+125	°C
Storage Temperature Range	TSTG	-40 to +125	°C

ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	CH501G-40GP	UNITS
Maximum Instantaneous Forward Voltage at If(1)= 10mA	VF(1)	0.34	Volts
Maximum Instantaneous Forward Voltage at If(2)= 100mA	VF(2)	0.55	Volts
Maximum Average Reverse Current at Vr= 10V	IR	30	uAmps

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 10.0 volts.
2. ESD sensitive product handling required.

2002-5

RATING CHARACTERISTIC CURVES (CH501G-40GP)

FIG. 1 - FORWARD CHARACTERISTICS

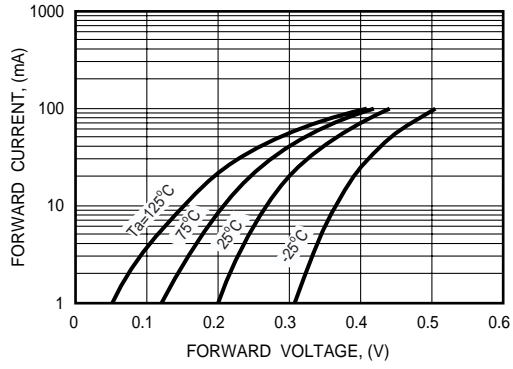


FIG. 2 - REVERSE CHARACTERISTICS

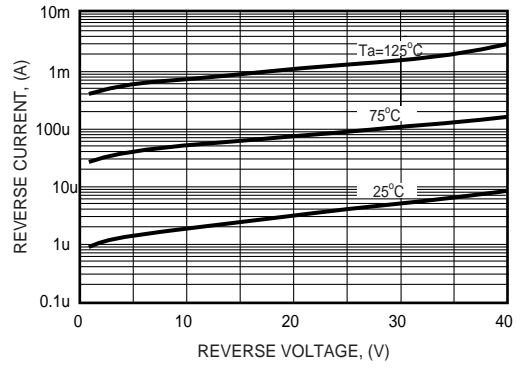


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

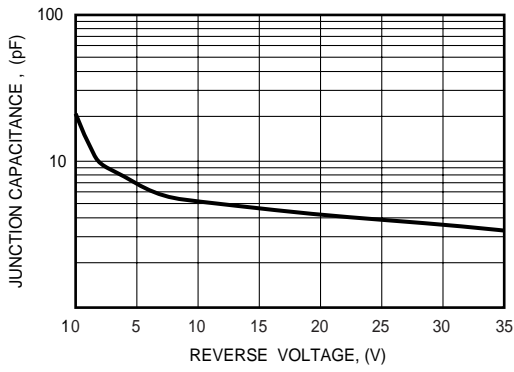


FIG. 4 - TYPICAL FORWARD CURRENT DERATING CURVE

